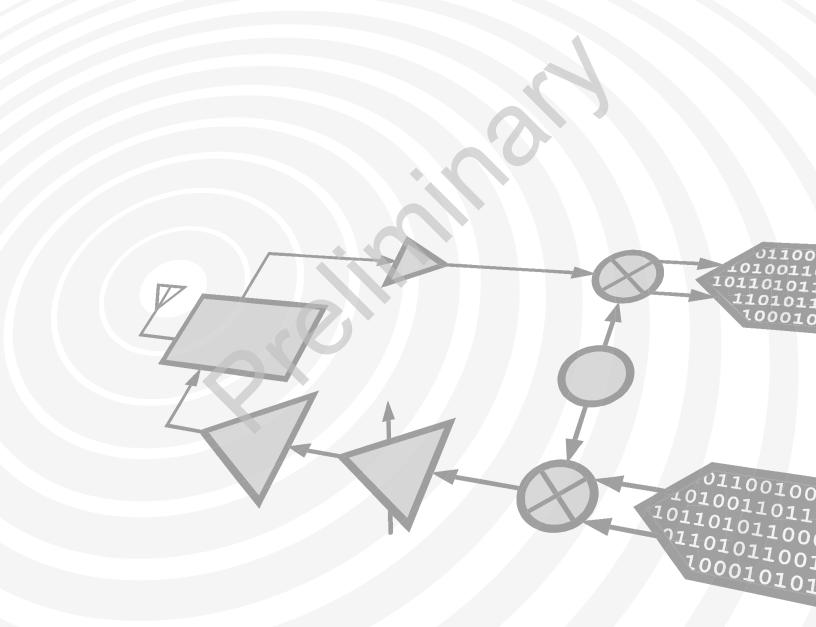




Analog Devices Welcomes Hittite Microwave Corporation



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HMC252AQS24 / 252AQS24E

v00.1115

GaAs MMIC SP6T NON-REFLECTIVE SWITCH, DC - 3 GHz

Typical Applications

The HMC252AQS24 / HMC252AQS24E is ideal for:

- Base Station
- CATV / DBS
- MMDS & WirelessLAN
- Test Equipment

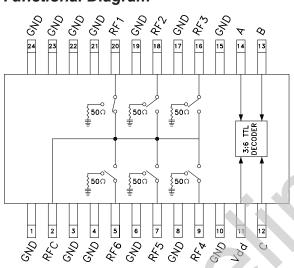
Features

Low Insertion Loss (2 GHz): 0.9 dB

Single Positive Supply: $V_{DD} = +5V \text{ or } +3.3V$

Integrated 3:6 TTL Decoder 24 Lead QSOP Package

Functional Diagram



General Description

The HMC252AQS24 & HMC252AQS24E are low-cost non-reflective SP6T switches in 24-lead QSOP packages featuring wideband operation from DC to 3.0 GHz. The switch offers a single positive bias and true TTL/CMOS compatibility. A 3:6 decoder is integrated on the switch requiring only 3 control lines and a positive bias to select each path. The HMC252AQS24 & HMC252AQS24E SP6T replaces multiple configurations of SP4T and SPDT MMIC switches and logic drivers.

Electrical Specifications I,

$T_A = +25$ °C, For TTL Control and $V_{DD} = +5V$ in a 50 Ohm System

Parameter	Frequency	Min.	Тур.	Max.	Units
Insertion Loss	DC - 1.0 GHz DC - 2.0 GHz DC - 2.5 GHz DC - 3.0 GHz		0.8 0.9 1.0 1.3	1.2 1.3 1.5 1.8	dB
Isolation	DC - 1.0 GHz DC - 2.0 GHz DC - 2.5 GHz DC - 3.0 GHz	38 32 29 26	41 35 32 29		dB
Return Loss "On State"	DC - 2.5 GHz DC - 3.0 GHz	14 7	18 12		dB
Return Loss RF1-6 "Off State"	0.3 - 3.0 GHz 0.5 - 2.5 GHz	8 11	12 15		dB
Input Power for 1dB Compression	0.3 - 3.0 GHz	21	24		dBm
Input Third Order Intercept (Two-Tone Input Power = +7 dBm Each Tone)	0.3 - 3.0 GHz	42	46		dBm
Switching Characteristics					
tRISE, tFALL (10/90% RF) tON, tOFF (50% CTL to 10/90% RF)	0.3 - 3.0 GHz		35 120		ns



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Electrical Specifications II,

 $T_A = +25^{\circ}\text{C}$, For TTL Control and $V_{DD} = +3.3\text{V}$ in a 50 Ohm System

Parameter		Frequency	Min.	Тур.	Max.	Units
Insertion Loss		DC - 1.0 GHz		0.8		dB
Isolation		DC - 1.0 GHz		41		dB
Return Loss	"On State"	DC - 1.0 GHz		21		dB
Return Loss	RF1-6 "Off State"	0.3 - 1.0 GHz		11		dB
Input Power for 1dB Compression		0.1 - 1.0 GHz		19		dBm

Bias Voltages & Currents

V _{DD} (V)	ldd (Typ.) (mA)	ldd (Max.) (mA)
+3.3 (Vdc ± 5%)	4.8	8
+5.0 (Vdc ± 10%)	5	8

TTL/CMOS Control Voltages

V _{DD} (V)	State	Bias Condition
. 2. 2	Low	0 to +0.8 Vdc @ 5μA Typ.
+3.3	High	+2.0 to +3.3 Vdc @ 70 μA Typ.
. 5.0	Low	0 to +0.8 Vdc @ 5μA Typ.
+5.0	High	+2.0 to +5 Vdc @ 70 μA Typ.

Truth Table

Control Input		Signal Path State	
Α	В	С	RFCOM to:
LOW	LOW	LOW	RF1
HIGH	LOW	LOW	RF2
LOW	HIGH	LOW	RF3
HIGH	HIGH	LOW	RF4
LOW	LOW	HIGH	RF5
HIGH	LOW	HIGH	RF6
LOW	HIGH	HIGH	ALL OFF
HIGH	HIGH	HIGH	ALL OFF

NOTE:

- 1. DC Blocking capacitors are required at ports RFC and RF1, 2, 3, 4, 5, 6.
- 2. Input is reflective when "ALL OFF" state is selected.



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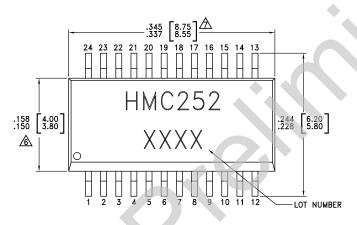
GaAs MMIC SP6T NON-REFLECTIVE SWITCH, DC - 3 GHz

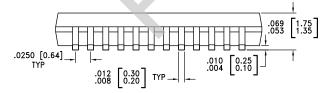
Absolute Maximum Ratings

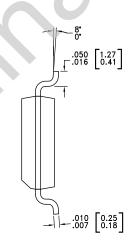
Bias Voltage Range (Port Vdd)	+7 Vdc
Control Voltage Range (A, B, C)	-0.5V to Vdd +1 Vdc
Channel Temperature	150 °C
Thermal Resistance (Insertion Loss Path)	117 °C/W
Thermal Resistance (Terminated Path)	210 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
Maximum Input Power Vdd = +5 Vdc	+20 dBm (0.05 - 0.5 GHz) +26 dBm (0.5 - 3.0 GHz)



Outline Drawing







- 1. PACKAGE BODY MATERIAL:LOW STRESS INJECTION MOLDED PLASTIC
- SILICA AND SILICON IMPREGNATED.
- 2. LEAD MATERIAL: COPPER ALLOY
- 3. LEAD PLATING: Sn/Pb SOLDER
- 4. DIMENSIONS ARE IN INCHES [MILLIMETERS]
- 5. CHARACTERS TO BE HELVETICA MEDIUM, .030 HIGH, WHITE INK,
- LOCATED APPROXIMATELY AS SHOWN.
- OIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.15mm PER SIDE. DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.25mm PER SIDE.
- 8. ALL GROUND LEADS MUST BE SOLDERED TO PCB RF GROUND.